2SK690

GaAs N-Channel MES FET

For UHF medium output power amplification

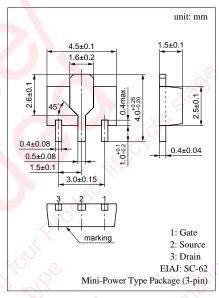
■ Features

- Large collector dissipation P_C
- Mini-power type package, allowing downsizing of the sets and automatic insertion through the tape/magazine packing.

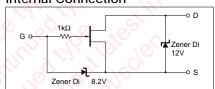
■ Absolute Maximum Ratings (Ta = 25°C)

| Parameter | Symbol | Ratings | Unit |
|-------------------------------|------------------|-------------|------|
| Drain to Source voltage | V _{DS} | 10 | V |
| Gate to Source voltage | V _{GS} | -6 | V |
| Drain current | I_{D} | 0.6 | A |
| Gate current | I_{G} | -1 | mA |
| Allowable power dissipation | P _D * | 1 | W |
| Channel temperature | T _{ch} | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |
| Operating ambient temperature | Topr | -35 to +85 | °C |

^{*} PC board: Copper foil of the drain portion should have a area of 1cm² or more and the board thickness should be 1.7mm.



Marking Symbol: M Internal Connection



■ Electrical Characteristics (Ta = 25°C)

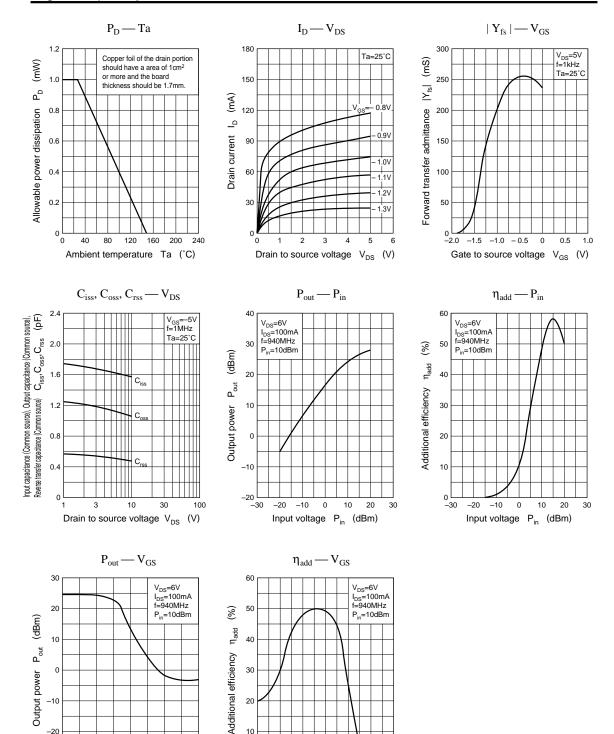
| Parameter | Symbol | Conditions | min | typ | max | Unit |
|--------------------------------|------------------|---|-----|-----|-----|------|
| Drain current | $I_{DD}^{*1, 2}$ | $V_{DS} = 5V, V_{GS} = 0$ | 150 | 350 | 600 | mA |
| Drain cut-off current | I_{DSX} | $V_{DS} = 10V, V_{GS} = -6V$ | 0 | | 2 | mA |
| Gate to Source leakage current | I _{GSS} | $V_{DS} = 0, V_{GS} = -6V$ | | | 50 | μΑ |
| Gate to Drain current | I_{GDO} | $V_{DS} = 16V$ | | | 500 | μА |
| Gate to Source cut-off voltage | V _{GSC} | $V_{DS} = 5V, I_{DS} = 1mA$ | | | -6 | V |
| Forward transfer admittance | Y _{fs} | $V_{DS} = 5V$, $I_{DS} = 50mA$, $f = 1kHz$ | 90 | 150 | | ms |
| Output power | P _{out} | V 6V I - 100m A | 20 | 25 | | dBm |
| Power gain | PG | $V_{DS} = 6V, I_{DS} = 100 \text{mA}$ $f = 940 \text{MHz}, P_{in} = 10 \text{dBm}$ | 10 | 15 | | dB |
| Additional efficiency | η_{add} | 1 = 940MHz, F _{in} = 10dBiii | | 51 | | % |

^{*1} IDSS rank classification

| Rank | P | Q | R |
|-----------------------|------------|------------|------------|
| I _{DSS} (mA) | 150 to 280 | 220 to 380 | 320 to 600 |

^{*2} Pulse measurement

Panasonic



2 **Panasonic**

(V)

-30 └ 0

-2

Gate to source voltage V_{GS}

-3

10

- 0.5 -1.0 -1.5 -2.0

Gate to source voltage V_{GS}

-2.5

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